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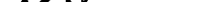
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary) #3				Complete if Known	
				Application Number	09/730586
				Filing Date	December 7, 2000
				First Named Inventor	AVNI, Dror
				Group Art Unit	unknown 2818
				Examiner Name	N/A
Sheet	1	of	2	Attorney Docket Number	P-2448-US1

[illegible][illegible]

Examiner Signature		Date Considered	2/28/02
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¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	unknown <i>09/130,586</i>
				Filing Date	December 7, 2000
				First Named Inventor	AVNI, Dror
				Group Art Unit	unknown <i>2812</i>
				Examiner Name	unknown
Sheet	2	of	2	Attorney Docket Number	P-2448-US1

[illegible]

Examiner Signature		Date Considered	2/28/02
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet

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of

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Application Number

09/730,586

Filing Date

December 7, 2000

First Named Inventor

AVNI, Dror

Group Art Unit

~~N/A~~ 2818

Examiner Name

N/A

Attorney Docket
Number

P-2448-US1

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**Examiner
Signature**

Date
Considered

2/28/02

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PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
P-2448-US1APPLICATION NO.
09/730,586SUPPLEMENTAL INFORMATION DISCLOSURE
STATEMENT BY APPLICANTSAPPLICANTS
Dror et al.CONFIRMATION NO.
9625FILING DATE
December 7, 2000

GROUP

2814

2818

U.S. PATENT DOCUMENTS

EXAM. INITIAL	DOC. NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (If Appropriate)
<i>bm</i>	3,895,360	07/15/1975	Cricchi et al.			
	4,016,588	04/05/1977	Ohya et al.			
	4,017,888	04/12/1977	Christie et al.			
	4,151,021	04/24/1979	McElroy			
	4,173,766	11/06/1979	Hayes			
	4,173,791	11/06/1979	Bell			
	4,257,832	03/24/1981	Schwabe et al.			
	4,306,353	12/22/1981	Jacobs et al.			
	4,342,149	08/03/1982	Jacobs et al.			
	4,360,900	11/23/1982	Bate			
	4,380,057	04/12/1983	Kotecha et al.			
	4,471,373	09/11/1984	Shimizu et al.			
	4,521,796	06/04/1985	Rajkaran et al.			
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	4,630,085	12/16/1986	Koyama			
	4,667,217	05/19/1987	Janning			
	4,742,491	05/03/1988	Liang et al.			
	4,769,340	09/06/1988	Chang et al.			
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	4,870,470	09/26/1989	Bass, Jr. et al.			
	4,941,028	07/10/1990	Chen et al.			
	5,021,999	06/04/1991	Kohda et al.			
	5,075,245	12/24/1991	Woo et al.			
	5,104,819	04/14/1992	Freiberger et al.			
	5,159,570	10/27/1992	Mitchell et al.			
	5,168,334	12/01/1992	Mitchell et al.			
	5,175,120	12/29/1992	Lee			
<i>bm</i>	5,214,303	05/25/1993	Aoki			

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EXAM. INITIAL	DOC. NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (If Appropriate)
<i>lms</i>	5,260,593	11/09/1993	Lee			
	5,305,262	04/19/1994	Yoneda			
	5,311,049	05/10/1994	Tsuruta			
	5,324,675	06/28/1994	Hayabuchi			
	5,349,221	09/20/1994	Shimoji			
	5,350,710	09/27/1994	Hong et al.			
	5,359,554	10/25/1994	Odake et al.			
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	5,654,568	08/05/1997	Nakao			
	5,656,513	08/12/1997	Wang et al.			
<i>lms</i>	5,712,814	01/27/1998	Fratin et al.			

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<i>HMA</i>	5,726,946	03/10/1998	Yamagata et al.			
	5,751,037	05/12/1998	Aozasa et al.			
	5,760,445	06/02/1998	Diaz			
	5,768,192	06/16/1998	Eitan			
	5,787,036	07/28/1998	Okazawa			
	5,793,079	08/11/1998	Georgescu et al.			
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	5,812,449	09/22/1998	Song			
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	5,841,700	11/24/1998	Chang			
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<i>HMA</i>	5,864,164	01/26/1999	Wen			
	5,870,333	02/09/1999	Khan et al.			
<i>HMA</i>	5,903,031	05/11/1999	Yamada et al.			
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	5,963,412	10/05/1999	En			
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	6,028,324	02/22/2000	Su et al.			
	6,030,871	02/29/2000	Eitan			
	6,034,403	03/07/2000	Wu			
<i>HMA</i>	6,034,896	03/07/2000	Ranaweera et al.			

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EXAM. INITIAL	DOC. NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (If Appropriate)
<i>hns</i>	6,063,666	05/16/2000	Chang et al.			
<i>hns</i>	6,201,282	03/13/2001	Eitan			12/23/1999
<i>hns</i>	08/905,286	07/30/1997	Eitan			
<i>hns</i>	09/082,280	05/20/1998	Eitan			
<i>hns</i>	09/348,720	07/06/1999	Eitan			
<i>hns</i>	09/413,408	10/06/1999	Eitan			
<i>hns</i>	09/536,125	03/28/2000	Eitan			

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FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
<i>hno</i>	EP 0751560	06/30/1995					
	EP 1073120	07/13/2000					
	GB 1297899	10/02/1970					
	GB 2157489	03/23/1984					
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	JP 07193151	12/27/1993					
	JP 09162314	12/12/1995					
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<i>hny</i>	WO 96/25741	02/16/1995					

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<i>W</i>	Bhattacharyya et al., "FET Gate Structure for Nonvolatile N-Channel Read-Mostly Memory Device," <u>IBM Technical Disclosure Bulletin</u> , U.S. IBM Corp. Volume 18, No. 6, page 1768, 1976.

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